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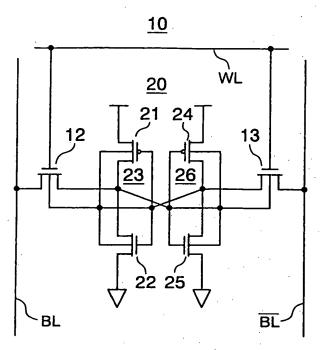
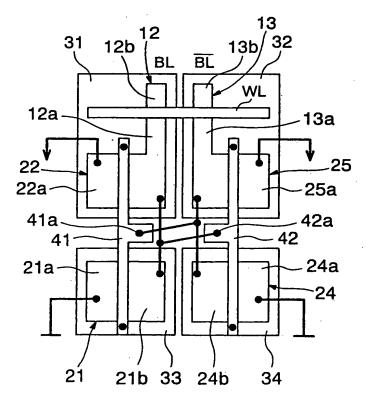


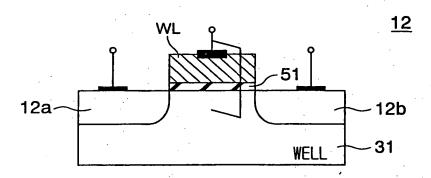
FIG.



F1G. 2

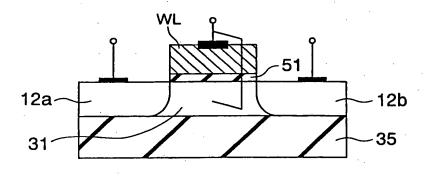
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USE OF ORDINARY SEMICONDUCTOR SUBSTRATE

FIG. 3A



USE OF SOI SUBSTRATE

FIG. 3B



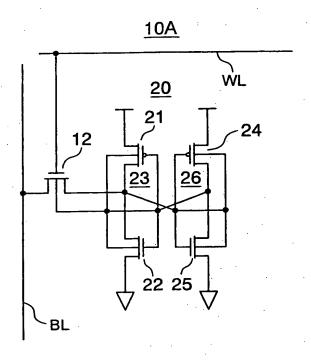


FIG. 4

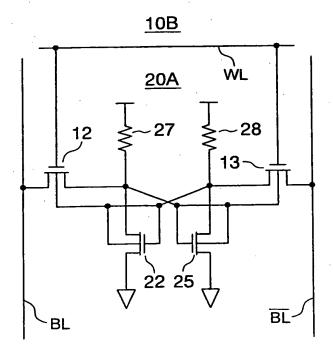


FIG. 5

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<u>10C</u>

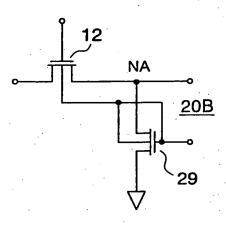
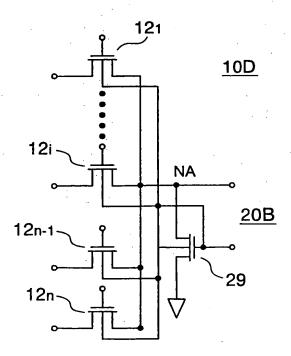


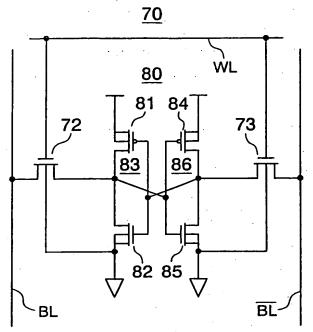
FIG. 6



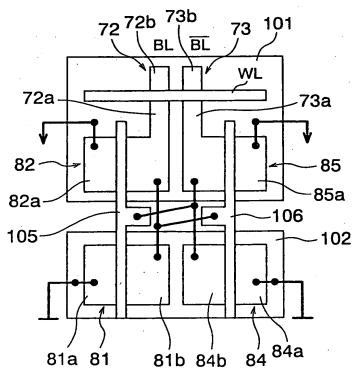
F1G. 7

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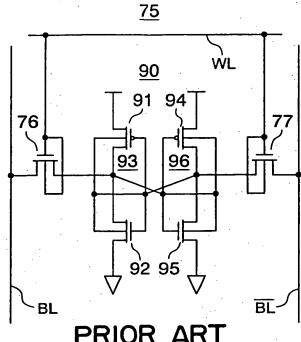
PRIOR ART FIG. 8



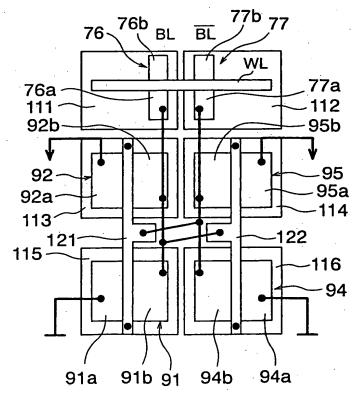
PRIOR ART FIG. 9

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PRIOR ART



PRIOR ART